MG300HF12TLE3

RoHS COMPLIANT

IGBT Modules

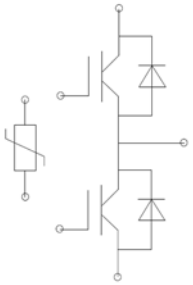


V_{CES}	1200V
I_C	300A

Applications

- Motion/servo control
- High frequency switching application
- UPS (Uninterruptible Power Supplies)
- Welding machine

Circuit



Features

- Low $V_{CE(sat)}$ with Trench technology
- Low switching losses especially Eoff
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability(10us)
- Including ultra fast & soft recovery anti-parallel FWD
- Low inductance package
- Maximum junction temperature 175℃

● IGBT

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	V_{GE}=0V, I_C=1mA, T_{vj}=25℃	1200	V
Continuous Collector Current	I_C	T_C=100℃	300	A
Repetitive Peak Collector Current	I_{CRM}	t_p=1ms	600	A
Gate-Emitter Voltage	V_{GES}	T_{vj}=25℃	±20	V
Total Power Dissipation	P_{tot}	T_C=25℃ T_{vjmax}=175℃	1850	W

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}$, I_C=11mA,T_{vj}=25℃	5.2	5.8	6.4	V
Collector-Emitter Cut-off Current	I_{CES}	V_{CE}=1200V,V_{GE}=0V,T_{vj}=25℃			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=300A,V_{GE}=15V, T_{vj}=25℃		1.90	2.30	V
		I_C=300A,V_{GE}=15V, T_{vj}=125℃		2.20		
		I_C=300A,V_{GE}=15V, T_{vj}=150℃		2.35		
Gate Charge	Q_G			2.65		uC
Internal Gate Resistance	R_{Gint}			1.25		Ω
Input Capacitance	C_{ies}	V_{CE}=25V,V_{GE}=0V, f=1MHz,T_{vj}=25℃		26.4		nF
Reverse Transfer Capacitance	C_{res}			0.81		nF
Gate-Emitter Leakage Current	I_{GES}	V_{CE}=0V, V_{GE}=20V,T_{vj}=25℃			400	nA
Turn-on Delay Time	$t_{d(on)}$	I_C=300A V_{CE}=600V V_{GE}=±15V R_G=1.3Ω T_{vj}=25℃		86		ns
Rise Time	t_r			58		ns
Turn-off Delay Time	$t_{d(off)}$			226		ns
Fall Time	t_f			190		ns
Energy Dissipation During Turn-on Time	E_{on}			26.3		mJ
Energy Dissipation During Turn-off Time	E_{off}			21.6		mJ
Turn-on Delay Time	$t_{d(on)}$	I_C=300A V_{CE}=600V V_{GE}=±15V R_G=1.3Ω T_{vj}=150℃		91		ns
Rise Time	t_r			64		ns
Turn-off Delay Time	$t_{d(off)}$			259		ns
Fall Time	t_f			246		ns
Energy Dissipation During Turn-on Time	E_{on}			37.8		mJ
Energy Dissipation During Turn-off Time	E_{off}			25.8		mJ
SC Data	I_{sc}	t_p≤10us, V_{GE}=15V, T_{vj}=150℃, V_{CC}=900V, V_{CEM}≤1200V		1200		A

Diode

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	T_{vj}=25℃	1200	V
Continuous DC Forward Current	I_F		300	A
Repetitive Peak Forward Current	I_{FRM}	t_p=1ms	600	A
I^2t-value	I^2t	V_R=0V,t_p=10ms,T_{vj}=125℃	18200	A^2s
		V_R=0V,t_p=10ms,T_{vj}=150℃	14500	

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	I_F=300A,T_{vj}=25℃		1.95		V
		I_F=300A,T_{vj}=125℃		1.80		
		I_F=300A,T_{vj}=150℃		1.75		
Recovered Charge	Q_{rr}	I_F=300A V_R=600V -di_F/dt=1800A/us T_{vj}=25℃		20.6		uC
Peak Reverse Recovery Current	I_{rr}			153		A
Reverse Recovery Energy	E_{rec}			7.4		mJ
Recovered Charge	Q_{rr}	I_F=300A V_R=600V -di_F/dt=1800A/us T_{vj}=150℃		47.2		uC
Peak Reverse Recovery Current	I_{rr}			210		A
Reverse Recovery Energy	E_{rec}			17.6		mJ

NTC-Thermistor

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	R_{25}			5.0		kΩ
Deviation of R100	ΔR/R	T_C=100,R_{100}=493.3Ω	-5		5	%
Power Dissipation	P_{25}				20.0	mW
B-value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$		3375		K

Module Characteristics

T_C=25°C unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	V_{isol}	t=1min,f=50Hz	2500			V
Maximum Junction Temperature	T_{jmax}				175	℃
Operating Junction Temperature	$T_{vj\ op}$		-40		150	℃
Storage Temperature	T_{stg}		-40		125	℃
Thermal Resistance Junction to Case	$R_{\theta JC}$	per IGBT			0.09	K/W
		per Diode			0.16	
Thermal Resistance Case to Sink	$R_{\theta CS}$	Conductive grease applied		0.009		K/W
Comparative Tracking Index	CTI		200			
Module Electrodes Torque	M_t	Recommended(M6)	4.0		5.0	N·m
Module to SinkTorque	M_s	Recommended(M5)	3.0		6.0	N·m
Weight of Module	G			345		g

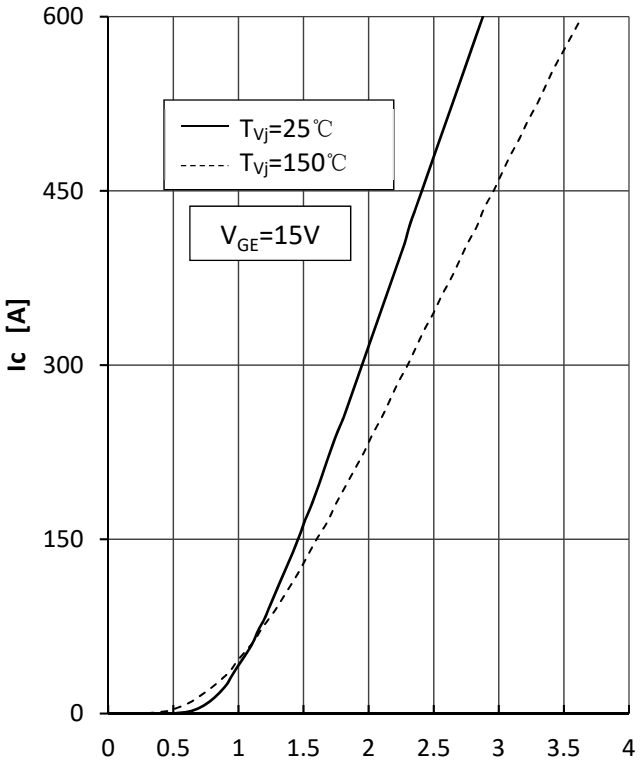


Fig1.IGBT Output Characteristics

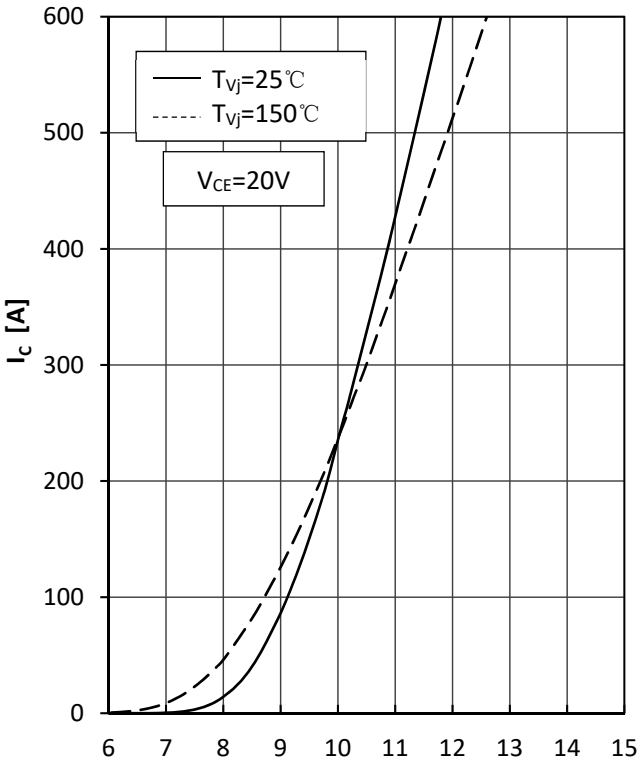


Fig2.IGBT Transfer Characteristics

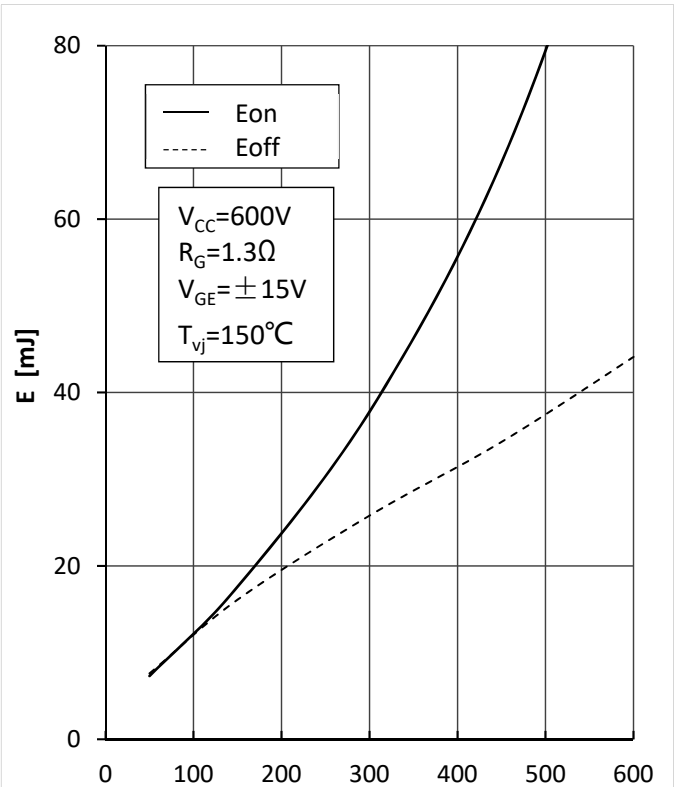


Fig3.IGBT Switching Loss vs.Ic

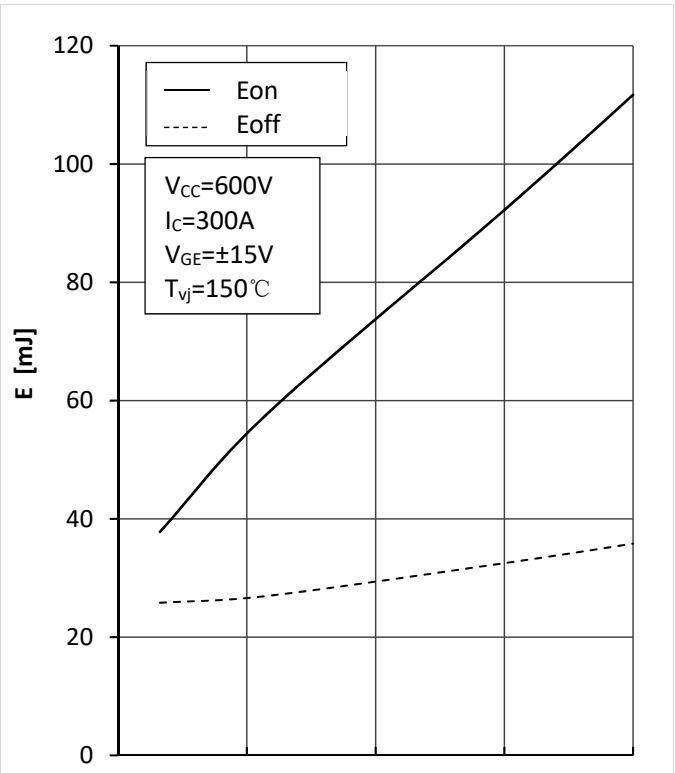


Fig4.IGBT Switching Loss vs.Rg

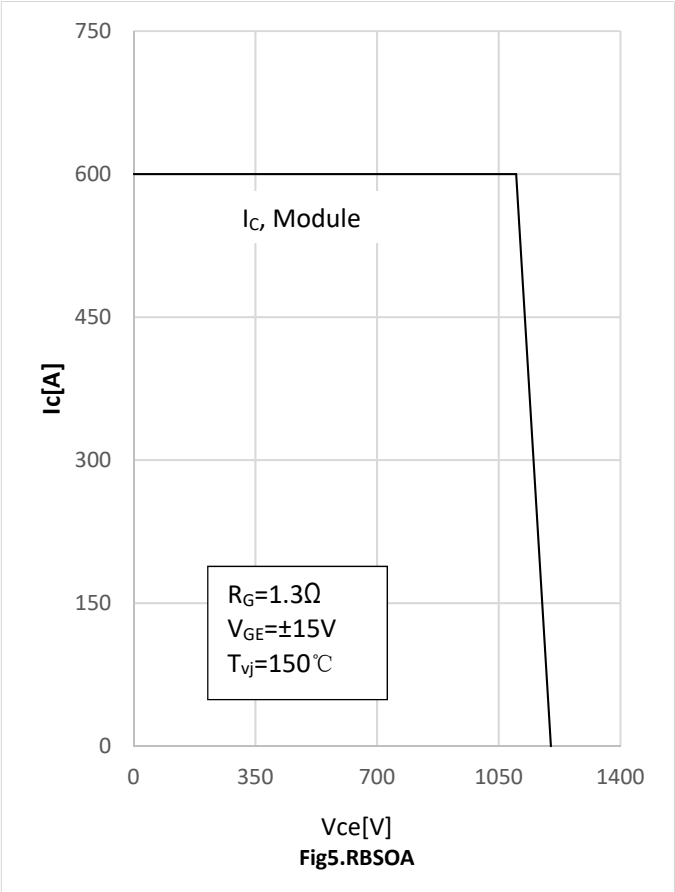


Fig5.RBSOA

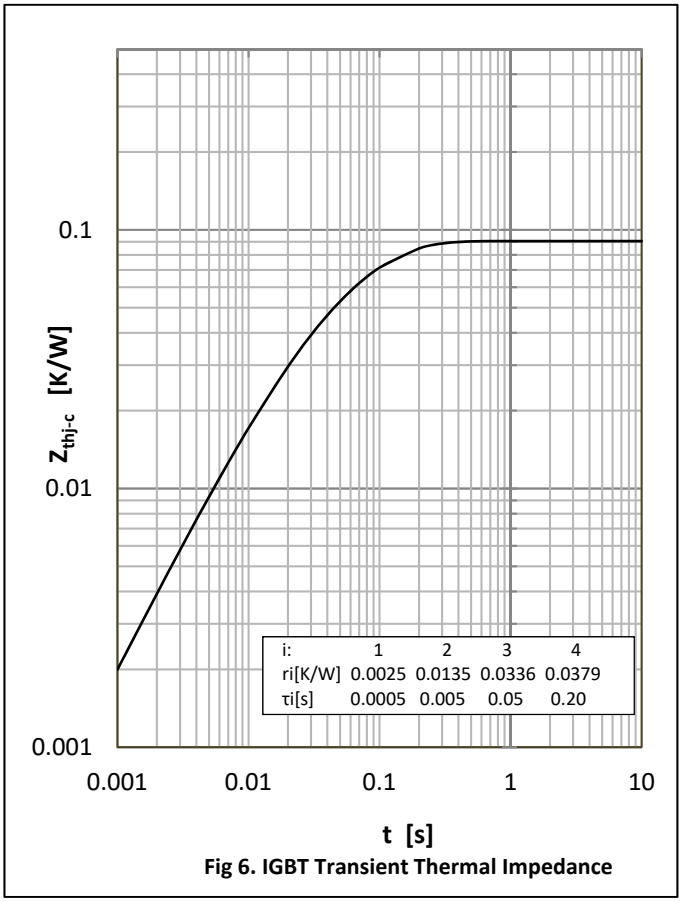


Fig 6. IGBT Transient Thermal Impedance

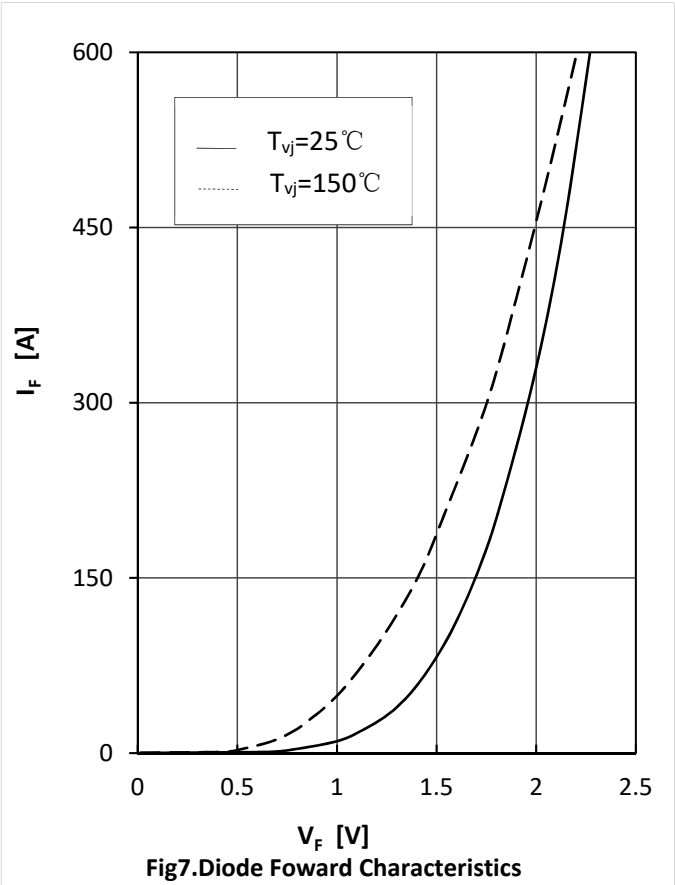


Fig7.Diode Foward Characteristics

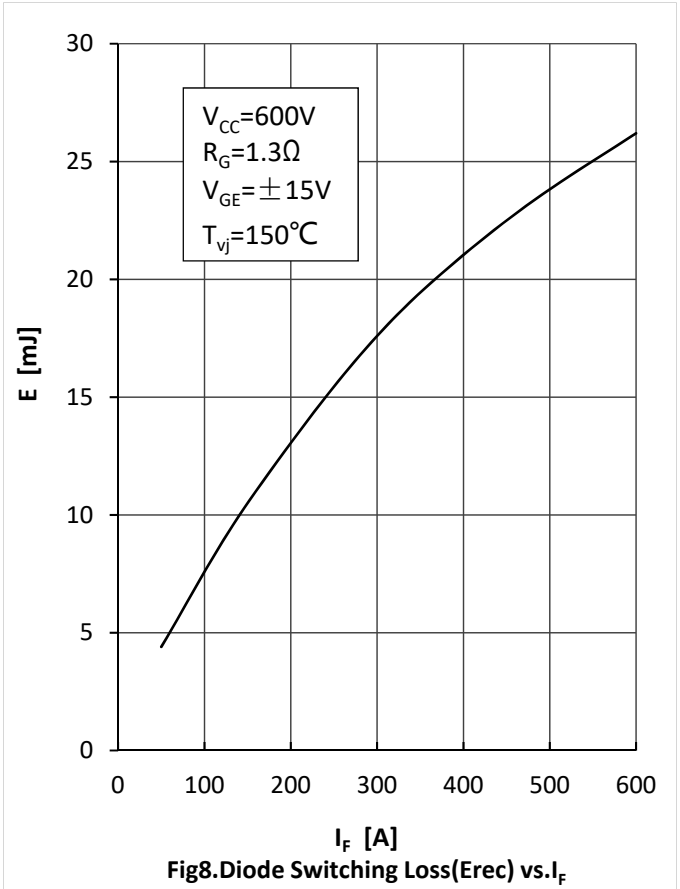


Fig8.Diode Switching Loss(Erec) vs.I_F

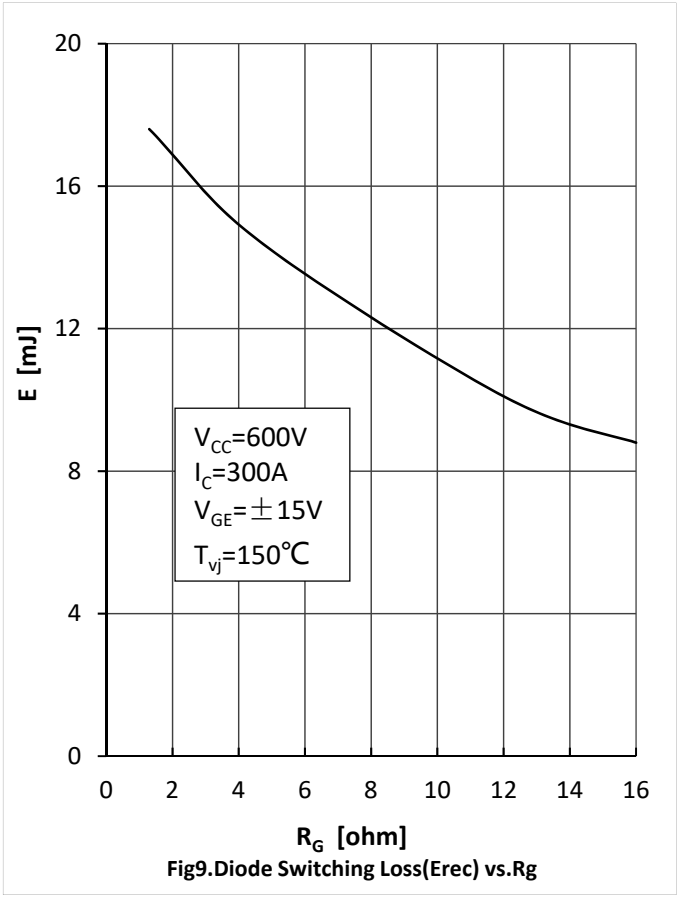


Fig9.Diode Switching Loss(Erec) vs.Rg

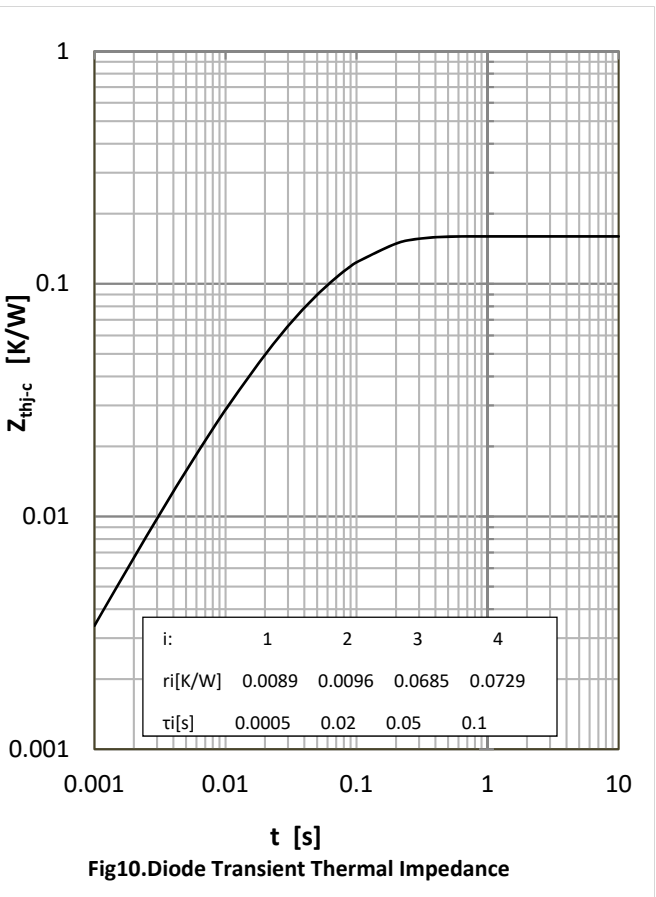


Fig10.Diode Transient Thermal Impedance

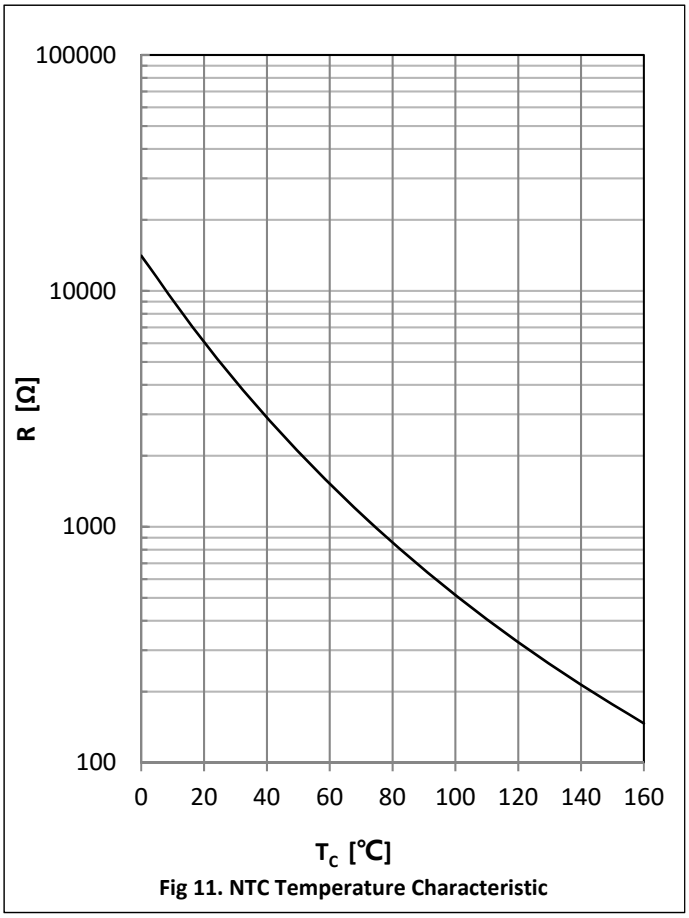
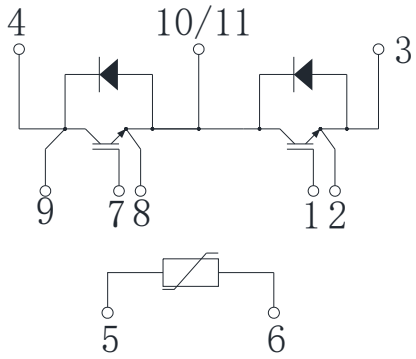
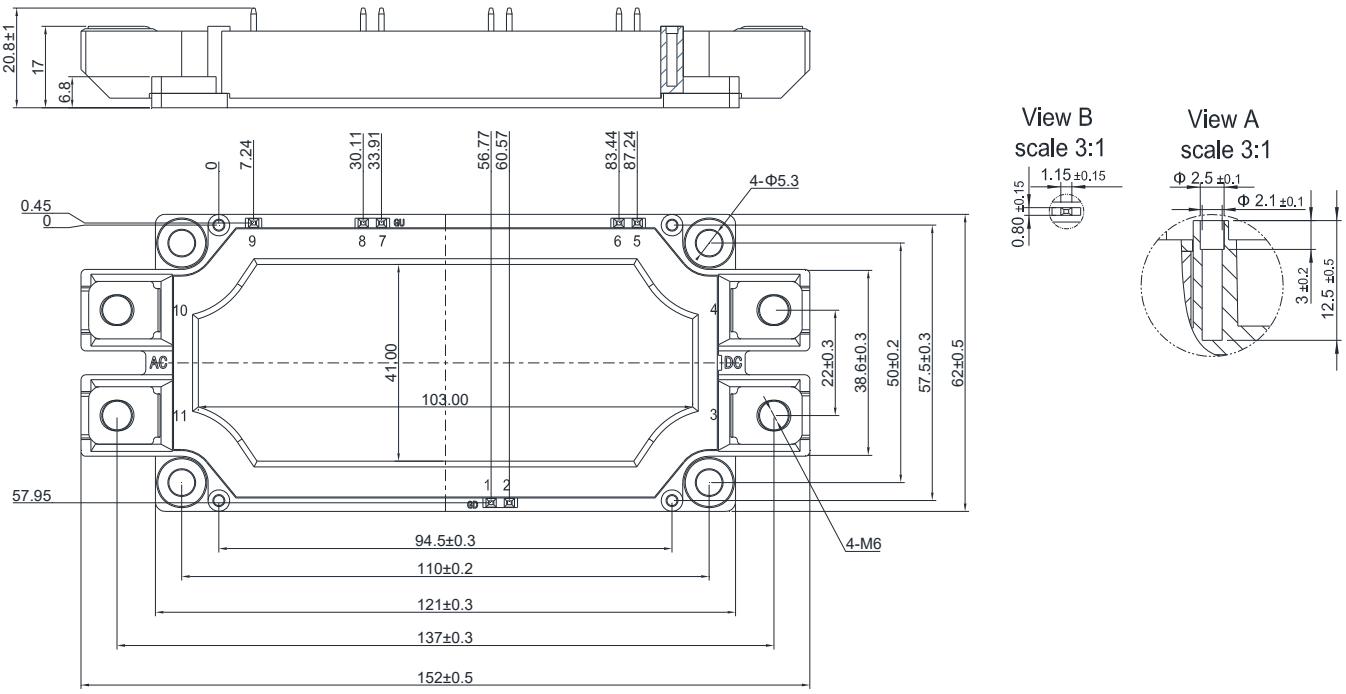


Fig 11. NTC Temperature Characteristic

- Circuit Diagram



- **Package Outline Information**



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